APPLICATIONS

Unit

W

Unit
V

I^2t T_J =125 , t=10ms, V_R=0V 39.2 KA^2S

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Unit

nA

		Unit
		V
		Nm
		Nm
		g

V_{CE} V

V_{GE} V

Figure 3. Typical Transfer characteristics IGBT-inverter

Rg q

Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

I_C A

Figure 5. Switching Energy vs Collector Current IGBT-inverter

V_{CE} V

Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

T_C( )

Figure 7. Collector Current vs Case temperature IGBT -inverter

T_C( )

Figure 8. Forward current vs Case temperature Diode -inverter

V_F(V)

Figure 9. Diode Forward Characteristics Diode -inverter

Rg q

Figure 10. Switching Energy vs Gate Resistor Diode - inverter

I_F(A)

Figure 11. Switching Energy vs Forward Current Diode-inverter

Rectangular Pulse Duration(S)

Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter